



DMTH4004SPS

40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Q _g Typ	I _D T _C = +25°C (Note 9)
40V	2.7mΩ @ V _{GS} = 10V	68.6nC	100A

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

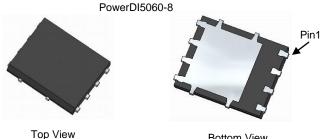
- **Engine Management Systems**
- **Body Control Electronics**
- DC-DC Converters

Features

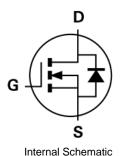
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_a Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH4004SPSQ)

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



Bottom View



Пο sΓ D Пο sГ Пп GΓ Top View Pin Configuration

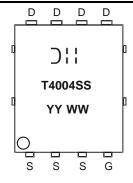
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4004SPS-13	PowerDI5060-8	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



⊃¦¦ = Manufacturer's Marking T4004SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 17 = 2017) WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	40	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	ID	31 26	А
$T_{C} = +25^{\circ}C$ Continuous Drain Current (Note 6) (Note 9)		Ι _D	100	А
$T_{C} = +100^{\circ}C$			100	<u> </u>
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I_{DM}	350	Α	
Maximum Continuous Body Diode Forward Current (Note 5)	Is	100	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	350	Α	
Avalanche Current, L=0.2mH	I _{AS}	45	Α	
Avalanche Energy, L=0.2mH	E _{AS}	200	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		P_{D}	3.6	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	41	°C/W
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P_{D}	167	W
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	0.9	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

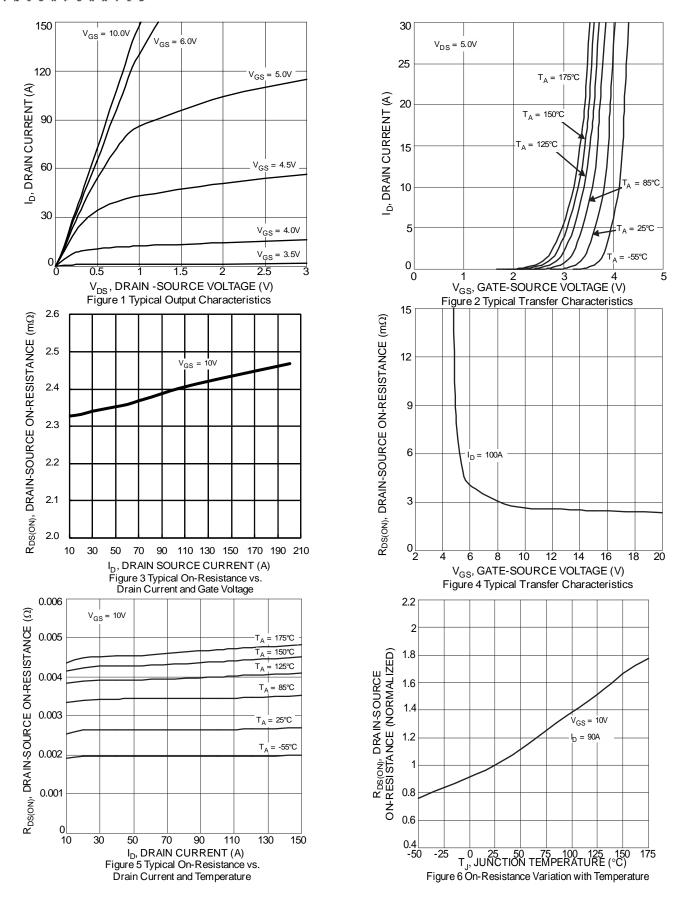
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	1	_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I_{GSS}	l	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	2	_	4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	1	2.3	2.7	mΩ	$V_{GS} = 10V, I_D = 90A$	
Diode Forward Voltage	V_{SD}		0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		4,305	_		V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	l	1,441		pF		
Reverse Transfer Capacitance	C_{rss}		102	_			
Gate Resistance	Rg	_	0.77	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{g}	_	68.6	_		$V_{DD} = 20V, I_D = 90A,$	
Gate-Source Charge	Q_{gs}	_	16.8	_	nC		
Gate-Drain Charge	Q_{gd}	_	14.2	_		V _{GS} = 10V	
Turn-On Delay Time	t _{D(ON)}	_	9.5	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 90A, R_{G} = 3.5\Omega$	
Turn-On Rise Time	t _R	_	6.7	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	26.4	_	115		
Turn-Off Fall Time	t _F	1	8.1	_			
Body Diode Reverse Recovery Time	t _{RR}	-	52.4	_	ns	I _F = 50A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}	1	78.2	_	nC	IF = 50A, αι/αι = 100A/μs	

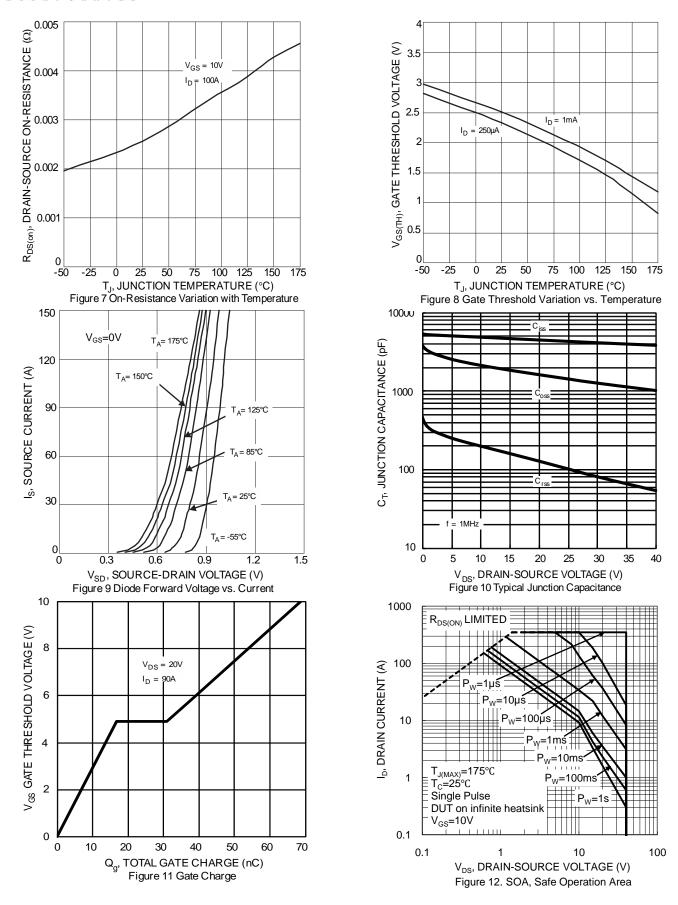
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).7 .Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.
- 9. Package limited.

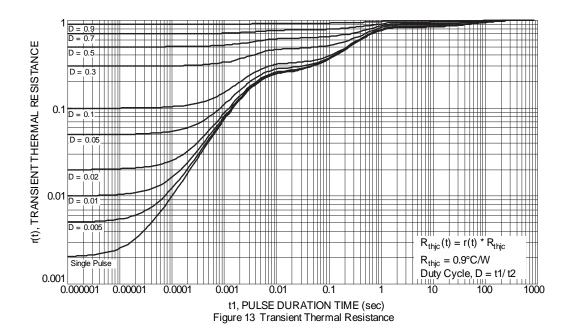










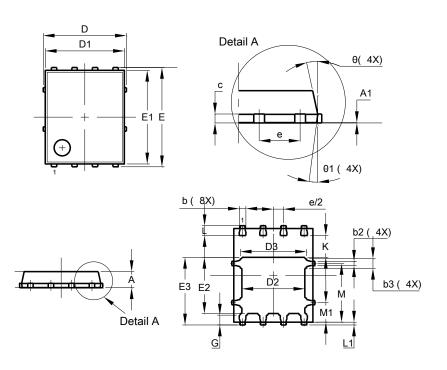




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

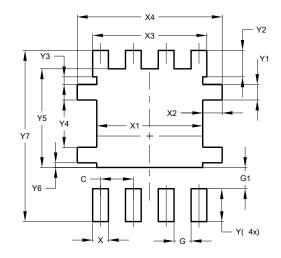


PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A 1	0.00	0.05	_	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D		5.15 BSC		
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	6.15 BSC			
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е	,	1.27 BSC		
G	0.51	0.71	0.61	
K	0.51	ı	_	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
М	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)				
С	1.270				
G	0.660				
G1	0.820				
X	0.610				
X1	4.100				
X2	0.755				
Х3	4.420				
X4	5.610				
Y	1.270				
Y1	0.600				
Y2	1.020				
Y3	0.295				
Y4	1.825				
Y5	3.810				
Y6	0.180				
Y7	6.610				



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